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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kern Rim

Docket: 16644

Patent No: 7,034,362

Dated: August 08, 2006

Issued: April 25, 2006

**For: DOUBLE SILICON-ONINSULATOR (SOI) METAL OXIDE
SEMICONDUCTOR FIELD EFFECT TRANSISTOR
(MOSFET) STRUCTURES**

**Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450**

**Certificate
AUG 16 2006
of Correction**

REQUEST FOR CERTIFICATE OF CORRECTION

Sir:

**It appearing that errors have been introduced in the course
of printing the Patent issued in the above application, it is respectfully
requested that the Commissioner issue a Certificate of Correction in
the following respects:**

Column 9 Line 35-36, Claim 2:

"and a spacer of the one isolation region located in the elevated device region"

should read

--and a spacer of the one semiconductor device located in the elevated device region--

Respectfully submitted,

**Leslie S. Szivos
Reg. No. 39,394**

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AUG 16 2006

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

PATENT NO : 7,034,362
APPLICATION NO : 10/688,692
ISSUE DATE : April 25, 2006
INVENTOR(S) : Kern Rim

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 9 Line 35-36, Claim 2:

“and a spacer of the one isolation region located in the elevated device region”

should read

--and a spacer of the one semiconductor device located in the elevated device region--

MAILING ADDRESS OF SENDER:

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PATENT No. 7,034,362

No. of additional copies

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AUG 16 2006